30V N-Channel MOSFETs

PDEC39I8BZ

General Description

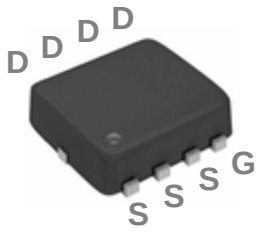
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

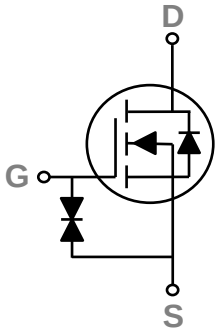
BVDSS	RDSON	ID
30V	7.9mΩ	35A

Features

- *30V,35A, RDS(ON) =7.9mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *Green Device Available*

PPAK3X3 Pin Configuration





Applications

- *Networking*
- *Load Switch*
- *LED applications*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	35	A
	Drain Current – Continuous (T_C=100℃)	22	A
I_{DM}	Drain Current – Pulsed[1]	140	A
EAS	Single Pulse Avalanche Energy[2]	24	mJ
IAS	Single Pulse Avalanche Current[2]	22	A
P_D	Power Dissipation (T_C=25℃)	21.5	W
	Power Dissipation – Derate above 25℃	0.17	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	5.8	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	μA
		V_{DS}=24V , V_{GS}=0V , T_J=85℃	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±20	μA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	6.6	7.9	mΩ
		V_{GS}=4.5V , I_D=15A	---	10	13	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	1.2	1.6	2.5	V

Dynamic and switching Characteristics[3]

Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=10V , I_D=20A	---	9.1	14	nC
		V_{DS}=15V , V_{GS}=4.5V , I_D=20A	---	4.6	7	
Q_{gs}	Gate-Source Charge		---	0.7	2	
Q_{gd}	Gate-Drain Charge		---	1.8	3.5	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=6Ω , I_D=20A	---	2	4	ns
T_r	Rise Time		---	2.5	5	
$T_{d(off)}$	Turn-Off Delay Time		---	4.5	9	
T_f	Fall Time		---	6.5	10	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , F=1MHz	---	440	650	pF
C_{oss}	Output Capacitance		---	320	500	
C_{rss}	Reverse Transfer Capacitance		---	23	35	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	0.5	---	Ω

Guaranteed Avalanche Energy

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V_{DD}=25V, L=0.1mH, I_{AS}=15.5A	12	---	---	mJ

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	35	A
I_{SM}	Pulsed Source Current		---	---	70	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_R=20V, I_S=10A	---	40	---	ns
Q_{rr}	Reverse Recovery Charge	di/dt=100A/μs , T_J=25℃	---	20	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=22A.,R_G=25Ω,Starting T_J=25℃.
3. Essentially independent of operating temperature.

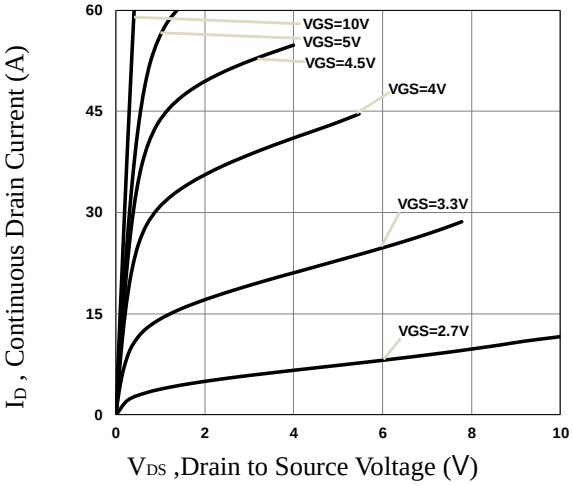


Fig.1 Typical Output Characteristics

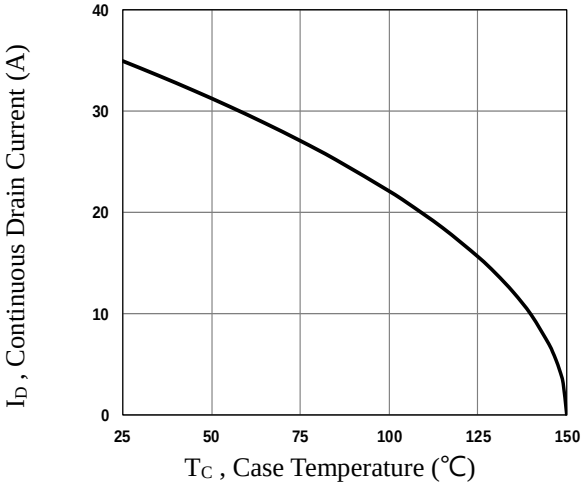


Fig.2 Continuous Drain Current vs. T_C

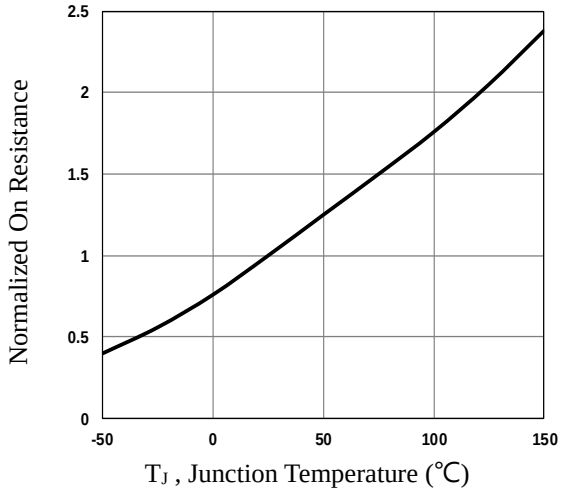


Fig.3 Normalized RDSON vs. T_J

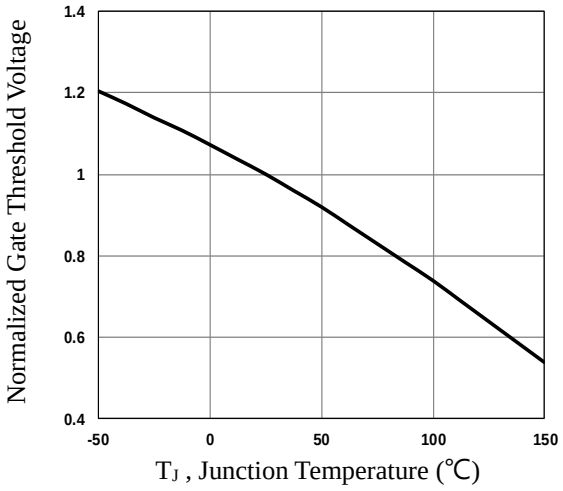


Fig.4 Normalized V_{th} vs. T_J

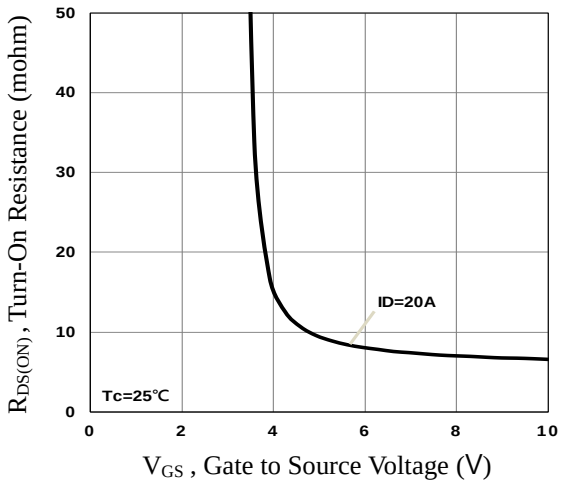


Fig.5 Turn-On Resistance vs. V_{GS}

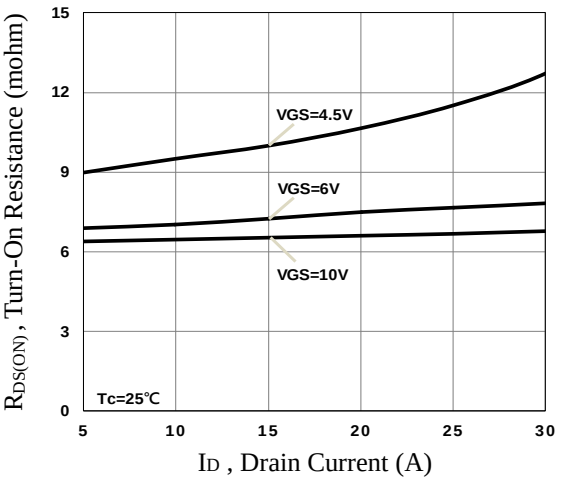


Fig.6 Turn-On Resistance vs. I_D

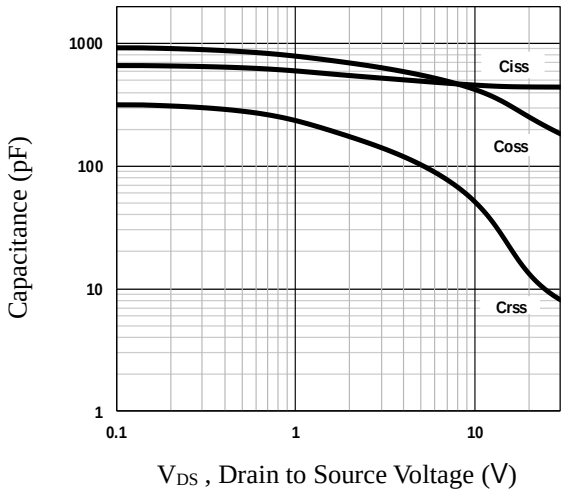


Fig.7 Capacitance Characteristics

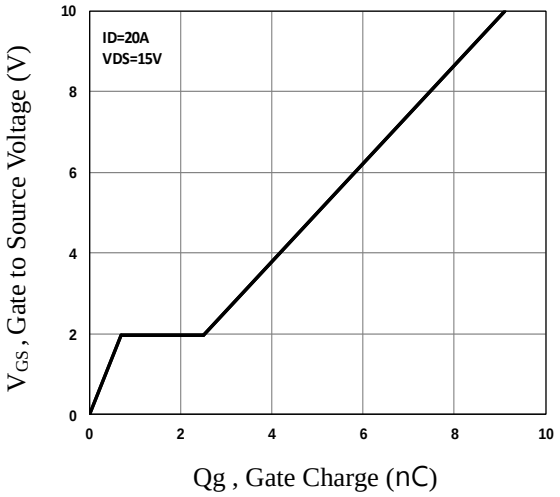


Fig.8 Gate Charge Characteristics

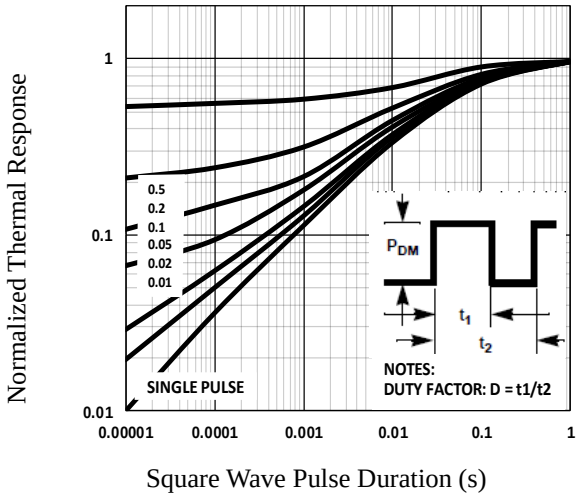


Fig.9 Normalized Transient Impedance

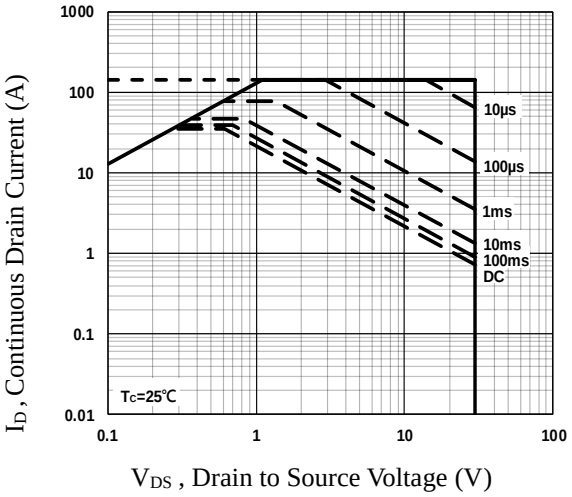


Fig.10 Maximum Safe Operation Area

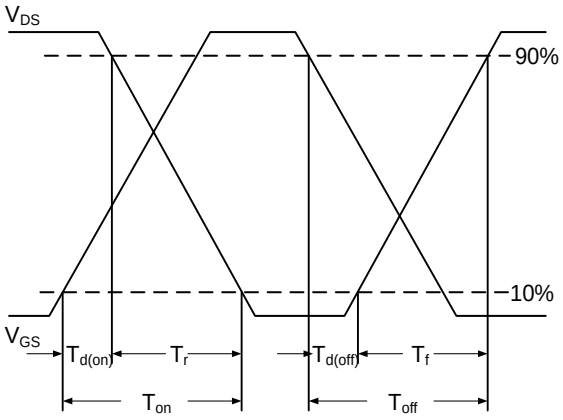


Fig.11 Switching Time Waveform

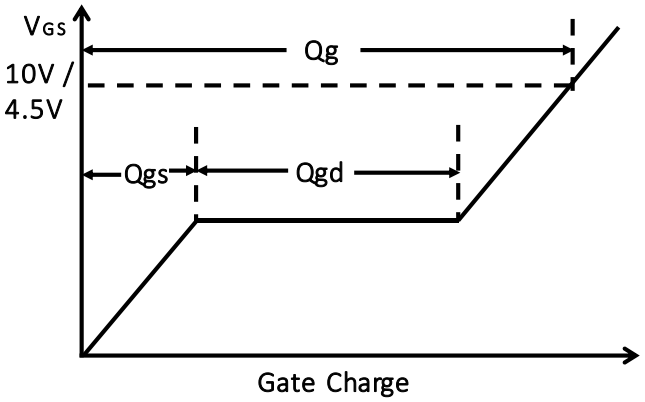
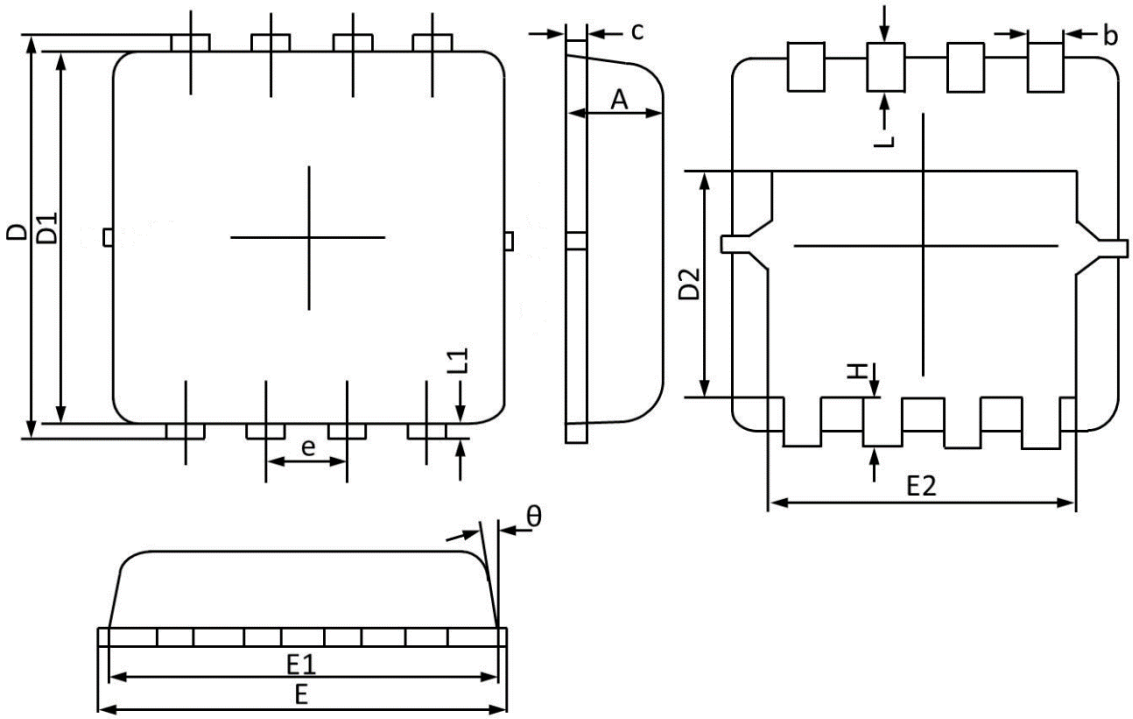


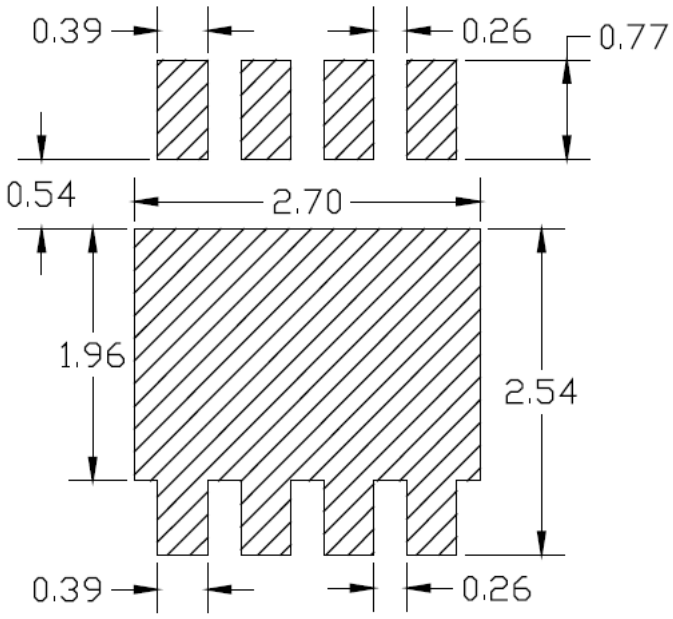
Fig.12 Gate Charge Waveform

PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.250	0.014	0.010
c	0.250	0.100	0.010	0.004
D	3.500	3.050	0.138	0.120
D1	3.200	2.900	0.126	0.114
D2	1.950	1.350	0.077	0.053
E	3.400	3.000	0.134	0.118
E1	3.300	2.900	0.130	0.114
E2	2.600	2.350	0.102	0.093
e	0.65BSC		0.026BSC	
H	0.750	0.300	0.030	0.012
L	0.600	0.300	0.024	0.012
L1	0.200	0.060	0.008	0.002
θ	14°	6°	14°	6°

PPAK3X3 RECOMMENDED LAND PATTERN



unit : mm